



## DOCUMENT CHANGE REQUEST

|            |             |                       |            |               |                    |
|------------|-------------|-----------------------|------------|---------------|--------------------|
| DCR number | 707         | Changes required for: | N/A        | Originator:   | Geraldine Chaumont |
| Date:      | 2012/09/03  | Date sent:            | 2012/02/10 | Organisation: | STMicroelectronics |
| Status:    | IMPLEMENTED |                       |            |               |                    |

Title: Transistors Low Power NPN, based on type 2N2222A

Number: 5201/002 Issue: 4

Other documents affected:

5201/004-4, 5202/001-6

Page:

5201/002: pages 6 & 16 - 5201/004: pages 5 & 13 - 5202/001: pages 5, 12 & 15

Paragraph:

5201/002: § 1.4.2, 2.9 & 2.10 - 5201/004: § 1.4.2, 2.9 & 2.10 - 5202/001: § 1.4.2, 2.4.1, 2.10 & 2.11

Original wording:

No irradiation data included in the detail specifications.

Proposed wording:

Insertion of new variants with radiation level + Insertion of Total dose radiation testing and Neutron testing paragraphs + Correction of a type error in the 5202/001.

Justification:

The customers are asking for a radiation level on bipolar transistors. At this time no radiation guarantee is included in the detail spec.

Attachments:

dc707\_attachment\_final\_version.docx, null

Modifications:

Modifications:

Replace the original DCR proposed wording by the following:

Addition of total dose radiation testing requirements for all Variants, to radiation level R 100kRAD(Si)

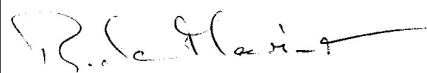
See final attachment for details of the changes & addition made to :

ESCC 5201/002 issue 4: Page 5, Para 1.4.1 & 1.4.2; Page 16, add new Para 2.9.

ESCC 5201/004 issue 4: Page 5, Para 1.4.1 & 1.4.2; Page 13, add new Para 2.9.

ESCC 5252/001 issue 6: Page 5, Para 1.4.1 & 1.4.2; Page 15, add new Para 2.10.

Approval signature:



Date signed:

2012-09-03